



IR Emitter and Detector Product Data Sheet

HSDL-4250

Spec No.: DS50-2008-0023

Effective Date: 06/18/2013

Revision: B

LITE-ON DCC

RELEASE

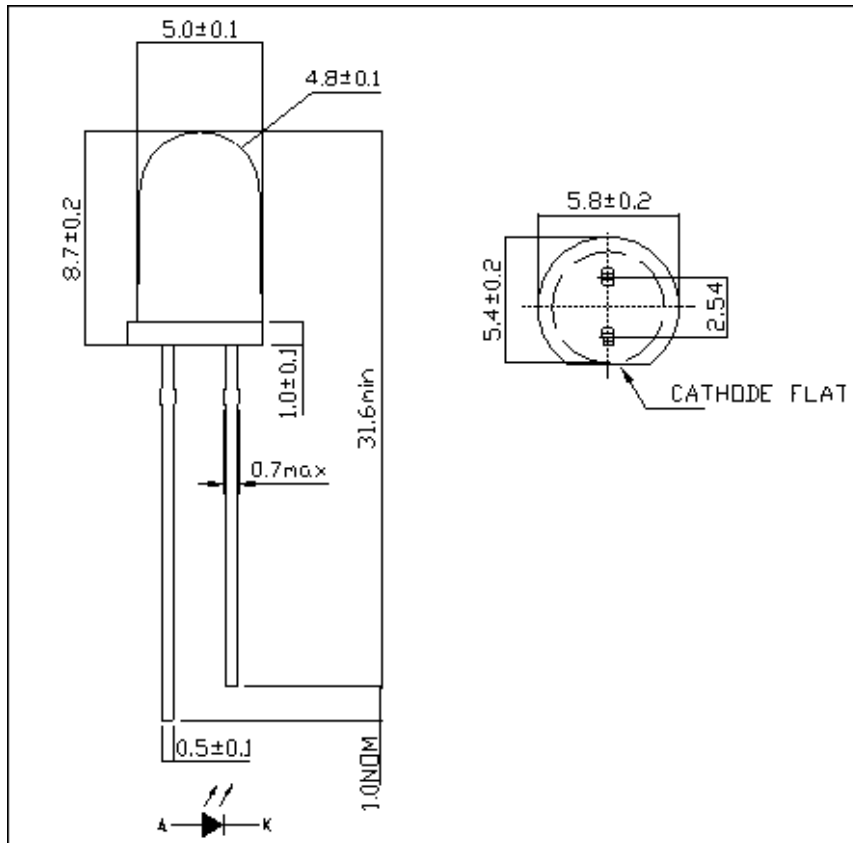
BNS-OD-FC001/A4

FEATURES

- | | |
|--|--|
| * High power AlGaAs LED technology | * Applications |
| * T-1 3/4 Package | High Speed IR communications |
| * 870 nm Wavelength | Portable Infrared Instruments |
| * High speed: 40ns Rise times | Consumer Electronics |
| * Low Forward Voltage | (Optical mouse, Infrared Remote Controllers ect) |
| * Low forward voltage for series operation | High Speed Infrared Communications |
| | (IR LANs , IR Moldens , IR Dongles , etc) |



PACKAGE DIMENSIONS



NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25\text{mm}(.010\text{'})$ unless otherwise noted.
3. Protruded resin under flange is $1.5\text{mm}(.059\text{'})$ max.
4. Lead spacing is measured where the leads emerge from the package.
5. Specifications are subject to change without notice.



LITE-ON TECHNOLOGY CORPORATION.

Property of Lite-On Only

ABSOLUTE MAXIMUM RATINGS AT TA=25°C

PARAMETER	Symbol	MIN	MAX	UNIT	Reference
Forward Current	I _{FDC}		100	mA	[1]
Peak Forward Current	I _{FPK}		500	mA	Fig 3 Duty Factor=20% Pulse Width=100us
Power Dissipation	P _{DISS}		190	mW	
Reverse Voltage	V _R	5		V	IR=100uA
Storage Temperature	T _S	-40	100	°C	
LED Junction Temperature	T _J		110	°C	
Lead Soldering Temperature [1.6mm(.063") From Body]			260 for 5 seconds	°C	

Notes:

1. Derate as shown in Figure 6.

Recommended Operating Conditions

PARAMETER	Symbol	MIN	MAX	UNIT	Reference
Operating Temperature	T _O	-40	85	°C	



LITE-ON TECHNOLOGY CORPORATION.

Property of Lite-On Only

ELECTRICAL CHARACTERISTICS AT 25°C

PARAMETER	Symbol	MIN.	TYP.	MAX.	UNIT	TEST CONDITION	Reference
Forward Voltage	V_F		1.4	1.6	V	$I_{FDC} = 20\text{mA}$	Fig.2
			1.5	1.9	V	$I_{FDC} = 100\text{mA}$	Fig.3
Forward Voltage Temperature Coefficient	$\Delta V / \Delta T$		-1.44		mV/°C	$I_{FDC} = 100\text{mA}$	Fig.4
Series Resistance	R_S		2.5		0hms	$I_{FDC} = 100\text{mA}$	
Diode Capacitance	C_O		75		pF	0 V, 1 MHz	
Reverse Voltage	V_R	2	20		V	$I_R = 100 \mu\text{A}$	
Thermal Resistance, Junction to Pin	$R \theta_{JA}$		300		°C/W		

OPTICAL CHARACTERISTICS AT TA=25°C

PARAMETER	Symbol	MIN.	TYP.	MAX.	UNIT	Test condition	Reference
Radiant On-Axis Intensity	I_E	124	180		Mw/Sr	$I_{FDC} = 100\text{mA}$	Fig.5
Radiant On-Axis Intensity Temperature Coefficient	$\Delta I_E / \Delta T$	-	-0.43	-	%/°C	$I_{FDC} = 100\text{mA}$	
Viewing Angle	$2\theta_{1/2}$	-	15	-	deg	$I_{FDC} = 50\text{mA}$	Fig.7
Peak Wavelength	λ_{pk}	-	870	-	nm	$I_{FDC} = 50\text{mA}$	Fig.1
Peak Wavelength Temperature Coefficient	$\Delta \lambda / \Delta T$	-	0.22	-	nm/°C	$I_{FDC} = 100\text{mA}$	
Spectral Width-at FWHM	$\Delta \lambda$		45	-	nm	$I_{FDC} = 50\text{mA}$	Fig.1
Optical Rise and all Times, 10%-90%	T_r / T_f		40	-	ns	$I_{FDC} = 500\text{ mA}$ Duty Ratio=20% Pulse Width=125ns	

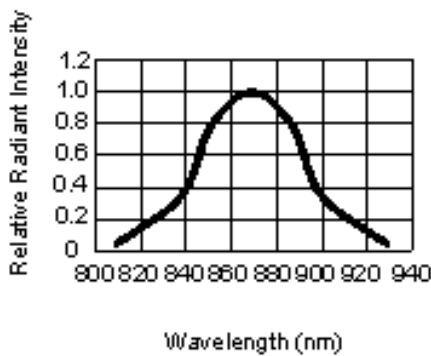


FIG.1 Relative Radiant Intensity VS Wavelength

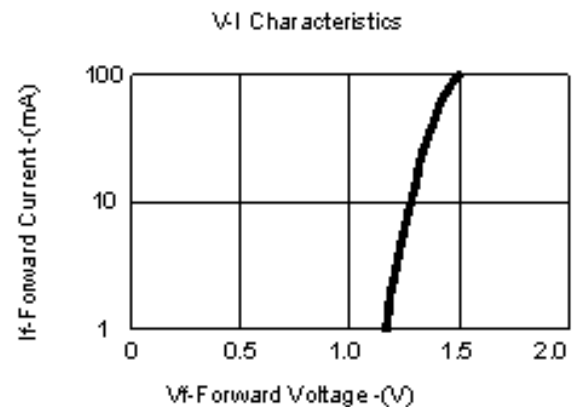


FIG.2 DC Forward Current VS. Forward Voltage

